

# Kazutoshi Kojima

## List of Publications by Citations

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131  
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135  
ext. papers

1,964  
ext. citations

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L-index

#	Paper	IF	Citations
131	Direct observation of dislocations propagated from 4H-SiC substrate to epitaxial layer by X-ray topography. <i>Journal of Crystal Growth</i> , <b>2004</b> , 260, 209-216	1.6	161
130	Effect of gate oxidation method on electrical properties of metal-oxide-semiconductor field-effect transistors fabricated on 4H-SiC C(0001) face. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 2088-2090	3.4	132
129	Impact ionization coefficients of 4H silicon carbide. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 1380-1382	3.4	95
128	Influence of growth conditions on basal plane dislocation in 4H-SiC epitaxial layer. <i>Journal of Crystal Growth</i> , <b>2004</b> , 271, 1-7	1.6	83
127	Excellent effects of hydrogen postoxidation annealing on inversion channel mobility of 4H-SiC MOSFET fabricated on (11 2 0) face. <i>IEEE Electron Device Letters</i> , <b>2002</b> , 23, 13-15	4.4	83
126	Dependence of acceptor levels and hole mobility on acceptor density and temperature in Al-doped p-type 4H-SiC epilayers. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 2708-2715	2.5	69
125	Epitaxial Growth of High-Quality 4H-SiC Carbon-Face by Low-Pressure Hot-Wall Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, L637-L639	1.4	56
124	Correlation between reliability of thermal oxides and dislocations in n-type 4H-SiC epitaxial wafers. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 022909	3.4	55
123	Homoepitaxial growth of 4H-SiC on on-axis C-face substrates by chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2004</b> , 269, 367-376	1.6	52
122	The Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors Fabricated on Cubic Silicon Carbide. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, L625-L627	1.4	34
121	N-channel MOSFETs fabricated on homoepitaxy-grown 3C-SiC films. <i>IEEE Electron Device Letters</i> , <b>2003</b> , 24, 466-468	4.4	32
120	The growth of low resistivity, heavily Al-doped 4H-SiC thick epilayers by hot-wall chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2013</b> , 380, 85-92	1.6	30
119	Defect-induced performance degradation of 4H-SiC Schottky barrier diode particle detectors. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 143714	2.5	24
118	Ultralow-Loss SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 1954-1960	2.9	23
117	Isotropic Channel Mobility in UMOSETs on 4H-SiC C-Face with Vicinal Off-Angle. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 999-1004	0.4	22
116	Influence of stacking faults on the performance of 4H-SiC Schottky barrier diodes fabricated on (112 0) face. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2974-2976	3.4	22
115	Development of SiC Super-Junction (SJ) Device by Deep Trench-Filling Epitaxial Growth. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 785-788	0.4	21

114	Development of SiC Super-Junction (SJ) Devices by Multi-Epitaxial Growth. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 845-850	0.4	20
113	Effect of Additional Silane on In Situ H <sub>2</sub> Etching prior to 4H-SiC Homoepitaxial Growth. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 85-88	0.4	20
112	4H-SiC MOSFETs on C(000-,1) Face with Inversion Channel Mobility of 127cm <sup>2</sup> /Vs. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 1417-1420	0.4	20
111	Challenges of High-Performance and High-Reliability in SiC MOS Structures. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 703-708	0.4	19
110	Effect of growth condition on micropipe filling of 4H-SiC epitaxial layer. <i>Journal of Crystal Growth</i> , <b>2005</b> , 275, e549-e554	1.6	19
109	Effects of Dislocations on Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 661-664	0.4	19
108	Low Resistivity, Thick Heavily Al-Doped 4H-SiC Epilayers Grown by Hot-Wall Chemical Vapor Deposition. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 181-184	0.4	18
107	Evaluation of 4H-SiC Thermal Oxide Reliability Using Area-Scaling Method. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 081404	1.4	18
106	Determination of carrier concentration by Fano interference of Raman scattering in heavily doped n-type 4H-SiC. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 043514	2.5	18
105	Determination of free carrier density in the low doping regime of 4H-SiC by Raman scattering. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 121913	3.4	16
104	Influence of basal-plane dislocation structures on expansion of single Shockley-type stacking faults in forward-current degradation of 4H-SiC p <sup>+</sup> n diodes. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 04FR07	1.4	15
103	4H-SiC Homoepitaxial Growth on Substrate with Vicinal Off-Angle Lower than 1°. <i>ECS Journal of Solid State Science and Technology</i> , <b>2013</b> , 2, N3012-N3017	2	15
102	Strong impact of slight trench direction misalignment from $\{11\bar{2}0\}$ on deep trench filling epitaxy for SiC super-junction devices. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 04CR05	1.4	14
101	Threshold Voltage Instability of SiC-MOSFETs on Various Crystal Faces. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 521-524	0.4	14
100	Microstructural Analysis of Damaged Layer Introduced during Chemo-Mechanical Polishing. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 370-373	0.4	14
99	Effects of n-type 4H-SiC epitaxial wafer quality on reliability of thermal oxides. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 6182-6184	3.4	14
98	High-Rate Epitaxial Growth of 4H-SiC Using a Vertical-Type, Quasi-Hot-Wall CVD Reactor. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 179-182	0.4	14
97	Filling 4H-SiC trench towards selective epitaxial growth by adding HCl to CVD process. <i>Applied Physics Express</i> , <b>2015</b> , 8, 065502	2.4	13

96	Linear energy transfer dependence of single event gate rupture in SiC MOS capacitors. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2014</b> , 319, 75-78	1.2	13
95	Analysis on Generation of Localized Step-Bunchings on 4H-SiC(0001)Si Face by Synchrotron X-Ray Topography. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 398-401	0.4	13
94	Filling of Deep Trench by Epitaxial SiC Growth. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 793-796	0.4	13
93	Decrease of Charge Collection Due to Displacement Damage by Gamma Rays in a 6H-SiC Diode. <i>IEEE Transactions on Nuclear Science</i> , <b>2007</b> , 54, 1953-1960	1.7	12
92	Influence of C/Si Ratio on the 4H-SiC (0001) Epitaxial Growth and a Keynote for High-Rate Growth. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 213-216	0.4	12
91	Modeling of SiC-CVD on Si-face/C-face in a horizontal hot-wall reactor. <i>Journal of Crystal Growth</i> , <b>2005</b> , 275, e515-e520	1.6	12
90	Epitaxial growth and characterization of thick multi-layer 4H-SiC for very high-voltage insulated gate bipolar transistors. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 085702	2.5	11
89	Origin analysis of expanded stacking faults by applying forward current to 4H-SiC p <sup>+</sup> n diodes. <i>Applied Physics Express</i> , <b>2017</b> , 10, 081201	2.4	11
88	E1/E2 traps in 6H-SiC studied with Laplace deep level transient spectroscopy. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 032104	3.4	11
87	Reducing Stacking Faults in Highly Doped N-Type 4H-SiC Crystal. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 8-11	0.4	11
86	Nitrogen incorporation characteristics on a 4H-SiC epitaxial layer. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 021907	0.4	11
85	Reverse characteristics of pn diodes on 4H-SiC(000-1) C and (11-20) face. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 1774-1776	3.4	11
84	Growth of silicon carbide epitaxial layers on 150-mm-diameter wafers using a horizontal hot-wall chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2013</b> , 381, 139-143	1.6	10
83	Influence of lattice polarity of nitrogen and aluminum doping on 4H-SiC epitaxial layer. <i>Microelectronic Engineering</i> , <b>2006</b> , 83, 79-81	2.5	10
82	Fabrication of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs) and their Electrical Properties. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 1175-1178	0.4	10
81	Effects of Pyrogenic Reoxidation Annealing on Inversion Channel Mobility of 4H-SiC Metal-Oxide-Semiconductor Field-Effect Transistor Fabricated on $\{11\bar{2}0\}$ Face. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, L1201-L1203	1.4	10
80	Synchrotron X-ray topography analysis of local damage occurring during polishing of 4H-SiC wafers. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 091301	1.4	9
79	An empirical growth window concerning the input ratio of HCl/SiH <sub>4</sub> gases in filling 4H-SiC trench by CVD. <i>Applied Physics Express</i> , <b>2017</b> , 10, 055505	2.4	9

78	Carrier Density Dependence of Fano Type Interference in Raman Spectra of p-type 4H-SiC. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 475-478	0.4	9
77	Transient Analysis of an Extended Drift Region in a 6H-SiC Diode Formed by a Single Alpha Particle Strike and Its Contribution to the Increased Charge Collection. <i>IEEE Transactions on Nuclear Science</i> , <b>2011</b> , 58, 305-313	1.7	9
76	Control of the Surface Morphology on Low Off Angled 4H-SiC Homoepitaxial Growth. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 113-116	0.4	9
75	Significant Improvement of Inversion Channel Mobility in 4H-SiC MOSFET on (11-20) Face Using Hydrogen Post-Oxidation Annealing. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1061-1064	0.4	9
74	Numerical analysis of the Gibbs-Thomson effect on trench-filling epitaxial growth of 4H-SiC. <i>Applied Physics Express</i> , <b>2016</b> , 9, 035601	2.4	8
73	Hopping conduction range of heavily Al-doped 4H-SiC thick epilayers grown by CVD. <i>Applied Physics Express</i> , <b>2015</b> , 8, 121302	2.4	8
72	Epitaxial Growth of Thick Multi-Layer 4H-SiC for the Fabrication of Very High-Voltage C-Face n-Channel IGBT. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 135-138	0.4	8
71	4H-SiC Homoepitaxial Growth on Vicinal-Off Angled Si-Face Substrate. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 99-102	0.4	8
70	Homoepitaxial Growth on a 4H-SiC C-Face Substrate. <i>Chemical Vapor Deposition</i> , <b>2006</b> , 12, 489-494		8
69	High Inversion Channel Mobility of 4H-SiC MOSFETs Fabricated on C(000-1) Epitaxial Substrate with Vicinal (Below 1°) Off-Angle. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 1043-1046	0.4	8
68	Ammonia-free high temperature metalorganic vapor phase epitaxy (AFHT-MOVPE): a new approach to high quality AlN growth. <i>CrystEngComm</i> , <b>2018</b> , 20, 7364-7370	3.3	8
67	Systematic investigation on in-plane anisotropy of surface and buried channel mobility of metal-oxide-semiconductor field-effect-transistors on Si-, a-, and m-face 4H-SiC. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 103506	3.4	7
66	Development of 4H-SiC Schottky np diode with high blocking voltage and ultralow on-resistance. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 012103	3.4	7
65	Suppression of short step bunching generated on 4H-SiC Si-face substrates with vicinal off-angle. <i>Journal of Crystal Growth</i> , <b>2014</b> , 401, 673-676	1.6	7
64	The Growth of 3-Inch 4H-SiC Si-Face Epitaxial Wafer with Vicinal Off-Angle. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 193-196	0.4	7
63	Investigation of In-Grown Dislocations in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 147-152	0.4	7
62	Simulation, Fabrication and Characterization of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 881-884	0.4	7
61	Suppression of 3-Inclusion Formation during Growth of 4-SiC Si-Face Homoepitaxial Layers with a 1° Off-Angle. <i>Materials</i> , <b>2014</b> , 7, 7010-7021	3.5	6

60	Electrical Properties of MOS Structures on 4H-SiC (11-20) Face. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 621-624	0.4	6
59	Charge Collection Efficiency of 6H-SiC P+N Diodes Degraded by Low-Energy Electron Irradiation. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 921-924	0.4	6
58	Doping Concentration Optimization for Ultra-Low-Loss 4H-SiC Floating Junction Schottky Barrier Diode (Super-SBD). <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 655-658	0.4	6
57	Charge Collection Properties of 6H-SiC Diodes by Wide Variety of Charged Particles up to Several Hundreds MeV. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 861-864	0.4	6
56	Improvement of Homoepitaxial Layer Quality Grown on 4H-SiC Si-Face Substrate Lower than 1 Degree Off Angle. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 141-144	0.4	6
55	Effect of Post-Oxidation Annealing in Wet O <sub>2</sub> and N <sub>2</sub> O Ambient on Thermally Grown SiO <sub>2</sub> /4H-SiC Interface for P-Channel MOS Devices. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 709-712	0.4	6
54	Impact Ionization Coefficients of 4H-SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 673-676	0.4	6
53	Uniformity of 4H-SiC epitaxial layers grown on 3-in diameter substrates. <i>Journal of Crystal Growth</i> , <b>2003</b> , 258, 113-122	1.6	6
52	2-Inch 4H-SiC Homoepitaxial Layer Grown on On-Axis C-Face Substrate by CVD Method. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 93-96	0.4	6
51	A Large Reduction in Interface-State Density for MOS Capacitor on 4H-SiC (11-20) Face Using H <sub>2</sub> and H <sub>2</sub> O Vapor Atmosphere Post-Oxidation Annealing. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1057-1060	0.4	6
50	Investigation of Residual Impurities in 4H-SiC Epitaxial Layers Grown by Hot-Wall Chemical Vapor Deposition. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 215-218	0.4	6
49	Homoepitaxial growth and investigation of stacking faults of 4H-SiC C-face epitaxial layers with a 1° off-angle. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 04DP04	1.4	6
48	Development of diagnostic method for deep levels in semiconductors using charge induced by heavy ion microbeams. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2015</b> , 348, 240-245	1.2	5
47	Electrical and physical characterizations of the effects of oxynitridation and wet oxidation at the interface of SiO <sub>2</sub> /4H-SiC(0001) and Si(0001). <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 04ER19	1.4	5
46	Influence of growth pressure on filling 4H-SiC trenches by CVD method. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 01AC04	1.4	5
45	Homo-Epitaxial Growth on 2° Off-Cut 4H-SiC(0001) Si-Face Substrates Using H <sub>2</sub> -SiH <sub>4</sub> -C <sub>3</sub> H <sub>8</sub> CVD System. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 214-217	0.4	5
44	Transient Currents Induced in 6H-SiC MOS Capacitors by Oxygen Ion Incidence. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 517-520	0.4	5
43	Epitaxial Growth of (11-20) 4H-SiC Using Substrate Grown in the [11-20] Direction. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 195-198	0.4	5



42	Experiment on alleviating the bending of CVD-grown heavily Al-doped 4H-SiC epiwafer by codoping of N. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 04DP08	1.4	4
41	Conversion of Basal Plane Dislocations to Threading Edge Dislocations in Growth of Epitaxial Layers on 4H-SiC Substrates with a Vicinal Off-Angle. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 99-102	0.4	4
40	C-Face Epitaxial Growth of 4H-SiC on Quasi-150-mm Diameter Wafers with High Throughput. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 109-112	0.4	4
39	Charge Enhancement Effects in 6H-SiC MOSFETs Induced by Heavy Ion Strike. <i>IEEE Transactions on Nuclear Science</i> , <b>2010</b> ,	1.7	4
38	A Long-Term Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 1269-1274	0.4	4
37	Control of Surface Morphologies for Epitaxial Growth on Low Off-Angle 4H-SiC (0001) Substrates. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 135-138	0.4	4
36	Replication of Defects from 4H-SiC Wafer to Epitaxial Layer. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 447-450	0.4	4
35	Reduction of background carrier concentration and lifetime improvement for 4H-SiC C-face epitaxial growth. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 081302	1.4	3
34	Characterization of the Defect Evolution in Thick Heavily Al-Doped 4H-SiC Epilayers. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 151-154	0.4	3
33	Single-Alpha-Particle-Induced Charge Transient Spectroscopy of the 6H-SiC $\text{p}^+\text{n}$ Diode Irradiated With High-Energy Electrons. <i>IEEE Transactions on Nuclear Science</i> , <b>2011</b> , 58, 3328-3332	1.7	3
32	Characterization of Electrical Properties in SiC Crystals by Raman Scattering Spectroscopy. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 501-504	0.4	3
31	Epitaxial Overgrowth of 4H-SiC for Devices with p-Buried Floating Junction Structure. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 147-150	0.4	3
30	Lifetime Control of the Minority Carrier in PIN Diodes by He <sup>+</sup> Ion Implantation. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 985-988	0.4	3
29	Thermometric quantum sensor using excited state of silicon vacancy centers in 4H-SiC devices. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 044001	3.4	3
28	Study of spiral growth on 4H-silicon carbide on-axis substrates. <i>Journal of Crystal Growth</i> , <b>2017</b> , 475, 251-255	1.6	2
27	Effect of Surface Orientation and Off-Angle on Surface Roughness and Electrical Properties of p-Type Impurity Implanted 4H-SiC Substrate after High Temperature Annealing. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 835-838	0.4	2
26	4H-SiC Carbon-Face Epitaxial Layers Grown by Low-Pressure Hot-Wall Chemical Vapor Deposition. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 209-212	0.4	2
25	Relationship between the Current Direction in the Inversion Layer and the Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors on 3C-SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 1405-1408	0.4	2

24	Electrical Properties of pn Diodes on 4H-SiC(000-1) C-Face and (11-20) Face. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 1065-1068	0.4	2
23	Observation of carrier lifetime distribution in 4H-SiC thick epilayers using microscopic time-resolved free carrier absorption system. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 105702	2.5	2
22	Investigation of Factors Influencing the Occurrence of 3C-Inclusions for the Thick Growth of on-Axis C-Face 4H-SiC Epitaxial Layers. <i>Materials</i> , <b>2020</b> , 13,	3.5	1
21	Characterization of stacking faults with emission wavelengths of over 500 nm formed in 4H-SiC epitaxial films. <i>Journal of Crystal Growth</i> , <b>2017</b> , 476, 99-106	1.6	1
20	Development of Homoepitaxial Growth Technique on 4H-SiC Vicinal Off Angled Substrate. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 125-130	0.4	1
19	Suppressing Al memory effect on CVD growth of 4H-SiC epilayers by adding hydrogen chloride gas. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 04EP07	1.4	1
18	Suppression of Al Memory-Effect on Growing 4H-SiC Epilayers by Hot-Wall Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CP04	1.4	1
17	Oxygen Ion Induced Charge in SiC MOS Capacitors Irradiated with Gamma-Rays. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 362-365	0.4	1
16	Gate-Area Dependence of SiC Thermal Oxides Reliability. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 787-790	0.4	1
15	Influence of Micropipe and Domain Boundary in SiC Substrate on the DC Characteristics of AlGaIn/GaN HFET. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 1043-1046	0.4	1
14	Influence of the Crystalline Quality of Epitaxial Layers on Inversion Channel Mobility in 4H-SiC MOSFETs. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1053-1056	0.4	1
13	SiC p+n Junction-Diodes toward Beam Monitor Applications. <i>IEEE Transactions on Nuclear Science</i> , <b>2021</b> , 1-1	1.7	1
12	Carrier dynamics of silicon vacancies of SiC under simultaneous optically and electrically excitations. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 021106	3.4	1
11	Investigation of Low Off-Angled 4H-SiC Epitaxial Wafers for Power Device Applications. <i>ECS Journal of Solid State Science and Technology</i> , <b>2017</b> , 6, P547-P552	2	0
10	Nondestructive measurements of depth distribution of carrier lifetimes in 4H-SiC thick epitaxial layers using time-resolved free carrier absorption with intersectional lights. <i>Review of Scientific Instruments</i> , <b>2020</b> , 91, 123902	1.7	0
9	Dependence of the Growth Parameters on the In-Plane Distribution of 150 mm Size SiC Epitaxial Wafer. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 139-142	0.4	
8	Peak Degradation of Heavy-Ion Induced Transient Currents in 6H-SiC MOS Capacitors. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 469-472	0.4	
7	Defects in an Electron-Irradiated 6H-SiC Diode Studied by Alpha Particle Induced Charge Transient Spectroscopy: Their Impact on the Degraded Charge Collection Efficiency. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 267-270	0.4	



- 6 Transient Response to High Energy Heavy Ions in 6H-SiC n+p Diodes. *Materials Science Forum*, **2008**, 600-603, 1039-1042 0.4
- 5 Challenges of 4H-SiC MOSFETs on the C(000-1) Face toward the Achievement of Ultra Low On-Resistance. *Materials Science Forum*, **2008**, 600-603, 907-912 0.4
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